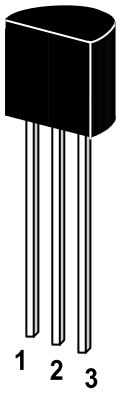
ST 2SC2655 (TO-92)

NPN Silicon Epitaxial Planar Transistor
for switching and AF amplifier applications.

The transistor is subdivided into two groups O and Y, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings (T_a=25°C)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	50	V
Collector Emitter Voltage	V_{CEO}	50	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	2	A
Power Dissipation	P_{tot}	900	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_s	-55 to +150	°C

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Characteristics at T_{amb}=25℃

		Symbol	Min.	Typ.	Max.	Unit
DC Current Gain						
at V_{CE}=2V, I_C=0.5A	O	h_{FE}	70	-	140	-
	Y	h_{FE}	120	-	240	-
at V_{CE}=2V, I_C=1.5A		h_{FE}	40	-	-	-
Collector Base Breakdown Voltage at I_C=1mA		$V_{(BR)CBO}$	50	-	-	V
Collector Emitter Breakdown Voltage at I_C=10mA		$V_{(BR)CEO}$	50	-	-	V
Emitter Base Breakdown Voltage at I_E=1mA		$V_{(BR)EBO}$	5	-	-	V
Collector Cutoff Current at V_{CB}=50V		I_{CBO}	-	-	1	μA
Emitter Cutoff Current at V_{EB}=5V		I_{EBO}	-	-	1	μA
Collector Saturation Voltage at I_C=1A, I_B=50mA		$V_{CE(sat)}$	-	-	0.5	V
Base Saturation Voltage at I_C=1A, I_B=50mA		$V_{BE(sat)}$	-	-	1.2	V
Gain Bandwidth Product at V_{CE}=2V, I_C=0.5A		f_T	-	100	-	MHz
Output Capacitance at V_{CB}=10V, f=1MHz		C_{OB}	-	40	-	pF